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AMENDMENTS TO THE CLAIMS:

This listing of claims replaces all prior versions and listings of claims in the application:

LISTING OF THE CLAIMS:

1 to 21. (Cancelled).

22. (Currently Amended) Circuitry for use in a mobile telephone, the circuitry comprising:

a terminal for use with a high-frequency signal;

at least two signal lines;

a switching unit for connecting the terminal to a signal line; and

a primary protection device for protecting against electrostatic discharges, the primary protection device being between the terminal and the switching unit, the primary protection device comprising a first element that diverts <u>all</u> voltages having a pulse height greater than <u>a 200V switching voltage</u> to a reference potential.

- 23. (Previously Presented) The circuitry of claim 22, wherein the first element has an insertion attenuation that is less than 0.3 dB.
- 24. (Previously Presented) The circuitry of claim 22, wherein the first element has a capacitance that is less than 1 pF.

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25. (Previously Presented) The circuitry of claim 22, wherein the first element comprises a gallium arsenide double diode.

26. (Previously Presented) The circuitry claim 22, wherein the primary protection device comprises a circuit path that connects the terminal and the switching unit; and

wherein the first element connects the circuit path to the reference potential.

27. (Previously Presented) The circuitry of claim 22, further comprising:

a second element that is in parallel with the first element, the second element for limiting a current load of the first element.

- 28. (Previously Presented) The circuitry of claim 27, further comprising: a capacitor on a circuit path between the first element and the second element
- 29. (Previously Presented) The circuitry of claim 27, wherein the second element comprises is a discharger.
- 30. (Previously Presented) The circuitry of claim 27, wherein the second element comprises a polymer suppressor.

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31. (Previously Presented) The circuitry of claim 27, wherein the second element comprises an over-voltage component having a capacitance that is less than 1 pF.

- 32. (Previously Presented) The circuitry of claim 27, wherein the second element comprises an inductive element having an inductance that is greater than 18 nH.
- 33. (Previously Presented) The circuitry of claim 22, further comprising: circuit paths that provide control signals to the switching unit, each of the circuit paths comprising a secondary protection device for protecting against electrostatic discharges.
- 34. (Previously Presented) The circuitry of claim 22, further comprising:

 a circuit path for supplying for an operating voltage to the switching unit, the
 circuit path comprising a secondary protection device for protecting against electrostatic
 discharges.
- 35. (Previously Presented) The circuitry of claim 22, wherein the switching unit comprises field effect transistors, a contact break distance of each of the field effect transistors connecting the terminal to a signal line; and

wherein the circuitry further comprises:

circuit paths that connect to gates of the field effect transistors, the circuit

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paths for providing control signals to the gates, each of the circuit paths comprising a secondary protection device for protecting against electrostatic discharges.

- 36. (Previously Presented) The circuitry of claim 33, 34 or 35, wherein the secondary protection device comprises a voltage-limiting element having a switching voltage that is less than 100 V.
- 37. (Previously Presented) The circuitry of claim 36, wherein the voltagelimiting element comprises a varistor.
- 38. (Previously Presented) The circuitry of claim 36, wherein the voltagelimiting element comprises a Zener diode.
- 39. (Previously Presented) The circuitry of claim 35, wherein at least one secondary protection device is connected to the reference potential.
- 40. (Previously Presented) The circuitry of claim 22, wherein the switching unit comprises PIN diodes.
- 41. (Previously Presented) The circuitry of claim 22, wherein the switching unit comprises a gallium arsenide switch.

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42. (Previously Presented) The circuitry of claim 22, wherein the terminal comprises an antenna input of a mobile telephone.

- 43. (Currently Amended) The circuitry of claim 22, wherein the signal lines comprises transmitting and receiving paths of a the mobile telephone.
- 44. (Previously Presented) The circuitry of claim 22, wherein the switching unit and the primary protection device are integrated into a multi-layer ceramic substrate.